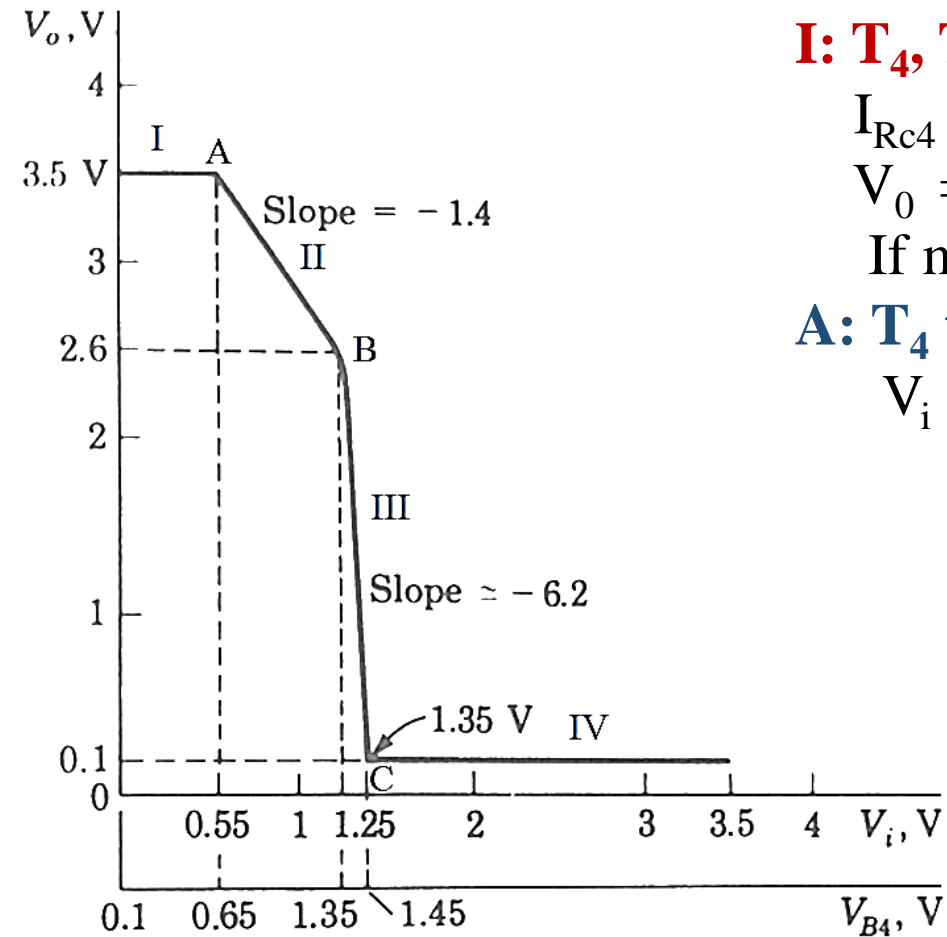


Digital Electronic Circuits

Section 1 (EE, IE)

Lecture 3

TTL: Transfer Characteristics



I: T_4, T_3 Cut-off. T_1 Sat., T_2 Active

$$I_{Rc4} = I_{B2} \text{ negligible}$$

$$V_0 = 5 - 2 \times 0.7 = 3.6 \text{ V}$$

$$\text{If more load, } V_0 = 5 - 2 \times 0.75 = 3.5 \text{ V}$$

A: T_4 turns on at $V_{BE4} = 0.65 \text{ V}$

$$V_i = 0.65 - V_{CE1(\text{Sat})} = 0.55 \text{ V}$$

II: T_4 active. T_3 Cut-off. T_1 Sat., T_2 Active

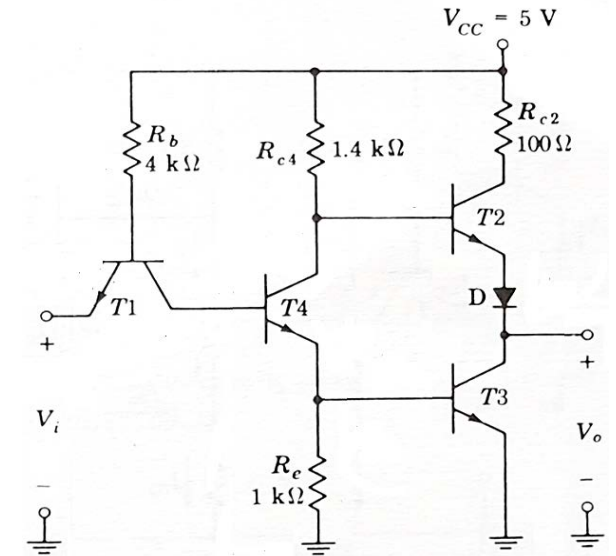
$$I_{RC4} \approx I_{C4} \text{ NOT negligible}$$

$$A_{V4} = - (R_{c4} / R_e) = -1.4$$

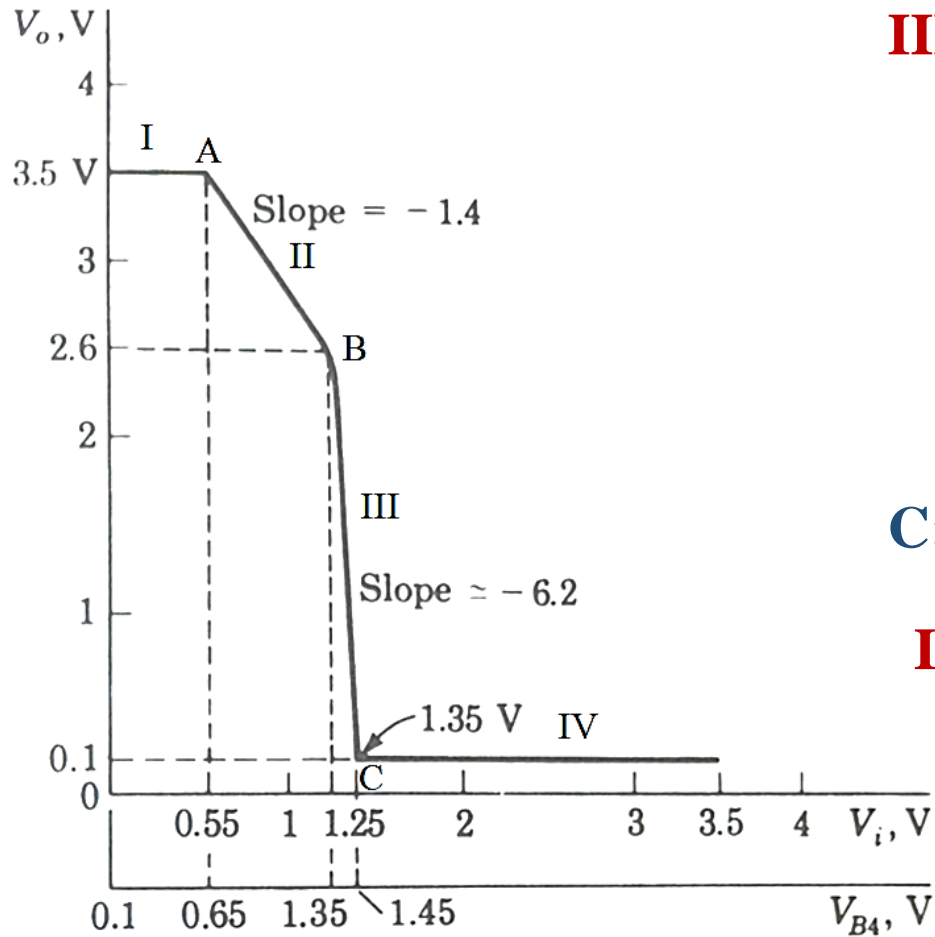
$$A_{V2} = 1 \text{ (emitter follower)}$$

B: T_3 turns on at $V_i = 0.7 + 0.65 - 0.1$

$$V_0 = 3.5 - (1.4 \times 0.65 / 1) = 2.6 \text{ V}$$



TTL: Transfer Characteristics



III: T_4 , T_3 Active. T_1 Sat. T_2 Active to Off

$$A_{V4} = - (R_{c4} / R_e \parallel r_d) = -2.8$$

$$A_{V3} = \Delta V_o / \Delta V_{B3} = - (\beta_F R_{c3(\text{eff.})} / r_d)$$

$$R_{c3(\text{eff.})} = (r_{d(D)} + r_{d(T2)} + R_{c4}) / \beta_F$$

$$A_{V3} = - (1.4 + 1 + 1) / 1 = -3.4$$

$$\Delta V_o = A_{V4} \Delta V_{B4} + A_{V3} \Delta V_{B3}$$

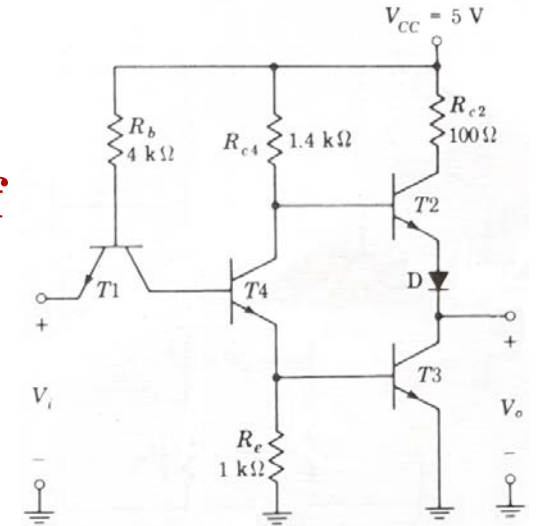
$$A_V = A_{V4} + A_{V3} = -6.2 \text{ [as } \Delta V_{B4} = \Delta V_{B3}]$$

C: T_3 saturates at $V_i = 0.75 + 0.7 - 0.1$ V

IV: T_4 , T_3 Sat. T_2 Cut-off. T_1 inverse

T_4 , T_3 saturate at $V_i = 2 \times 0.75 - 0.1$ V

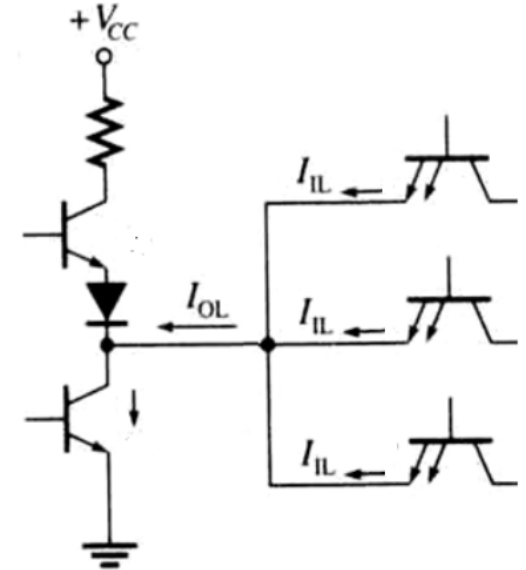
$$V_o = 0.1 \text{ V}$$



SN7404 Datasheet

Texas Instruments (Revised 2004)

Parameter	Min.	Typical	Max.	Unit
V_{IH}	2			V
V_{IL}			0.8	V
I_{OH}			-0.4	mA
I_{OL}			16	mA
V_{OH}	2.4	3.4		V
V_{OL}		0.2	0.4	V
I_{IH}			40	μ A
I_{IL}			-1.6	mA
t_{PLH}		12	22	ns
t_{PHL}		8	15	ns



Fanout = Lower [$|I_{OH}/I_{IH}|$, $|I_{OL}/I_{IL}|$] = 10

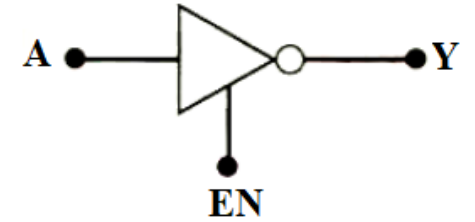
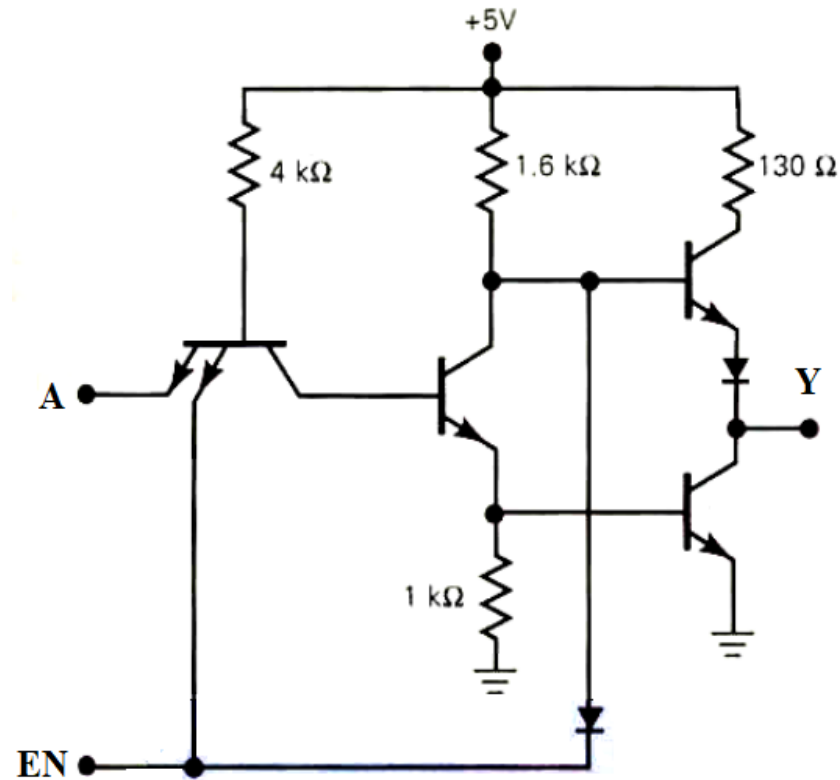
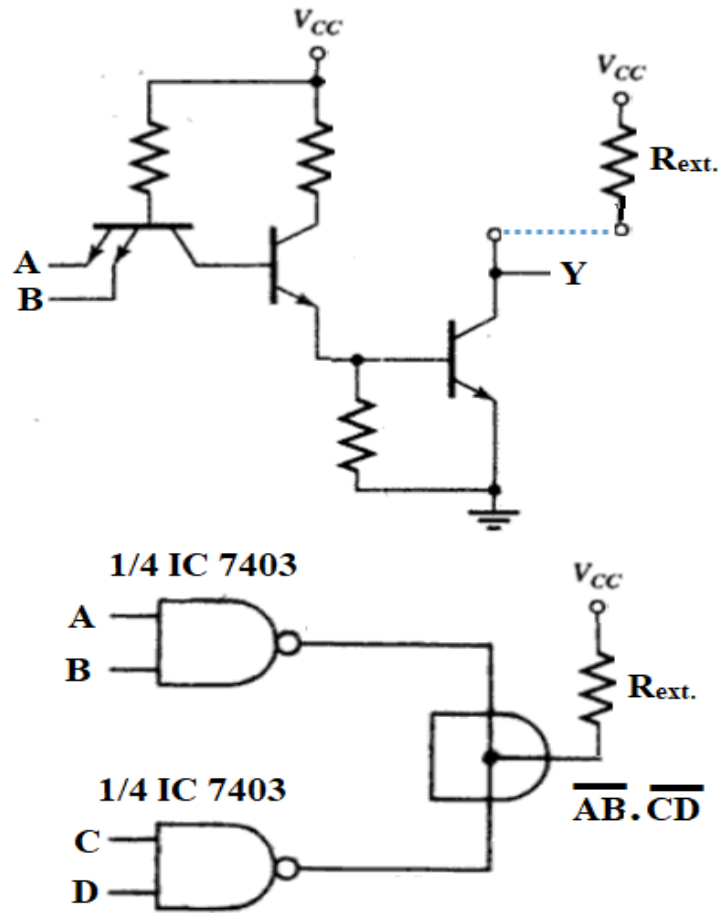
$$NM_L = V_{IL} - V_{OL} = 0.8 - 0.4 = 0.4V$$

$$NM_H = V_{OH} - V_{IH} = 2.4 - 2 = 0.4V$$

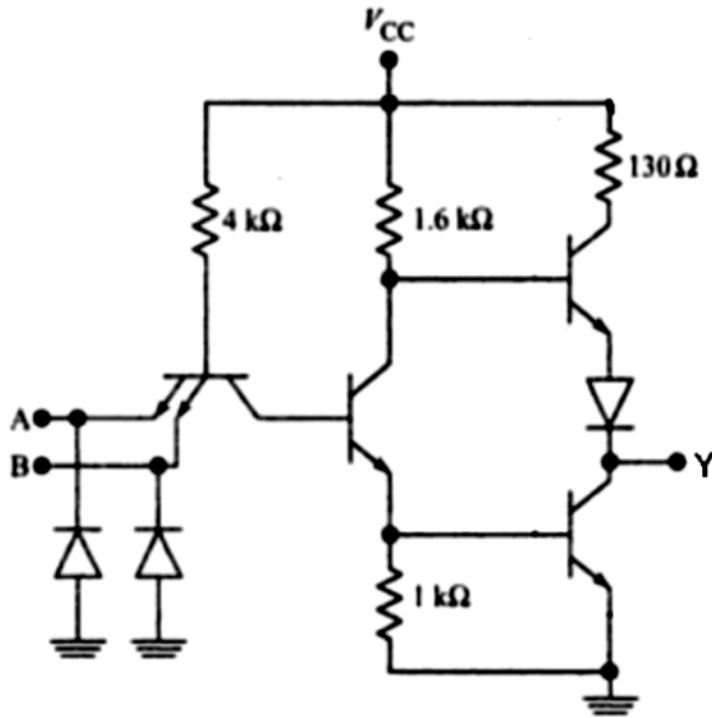
$$P_D = 10mW$$

Note: Under specific test condition
e.g. $R_L=400\Omega$, $C_L=15pF$

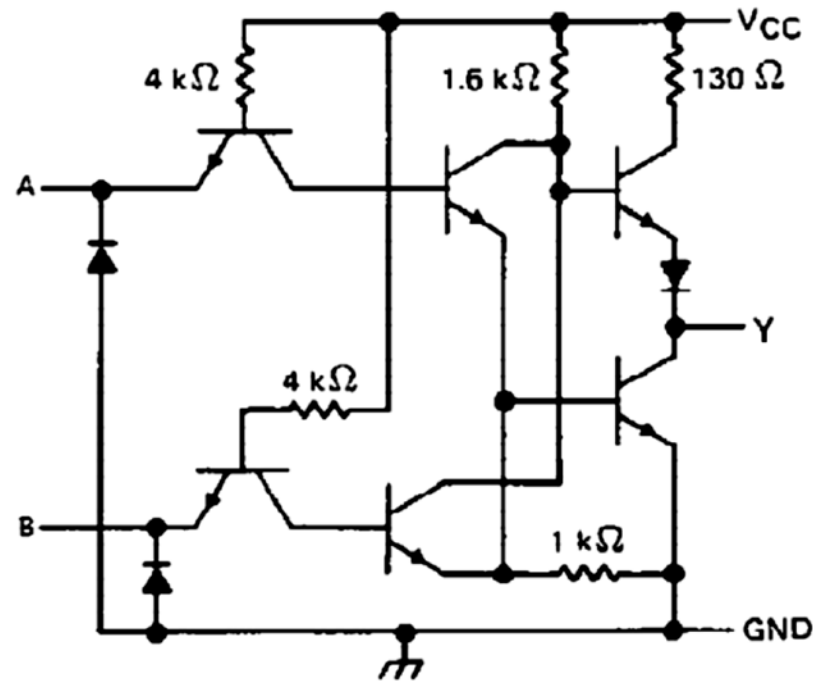
TTL: Open Collector, Tri-state



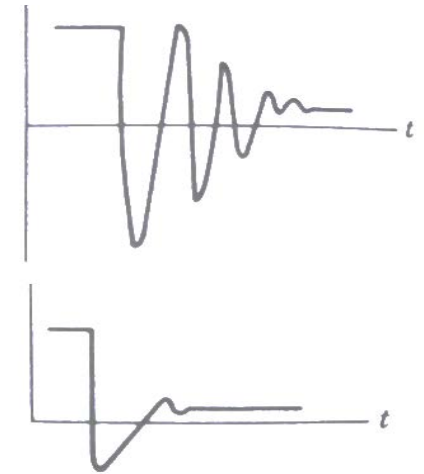
TTL Gates: NAND, NOR



2-input NAND gate



From TI SN7402 (2-input NOR) datasheet

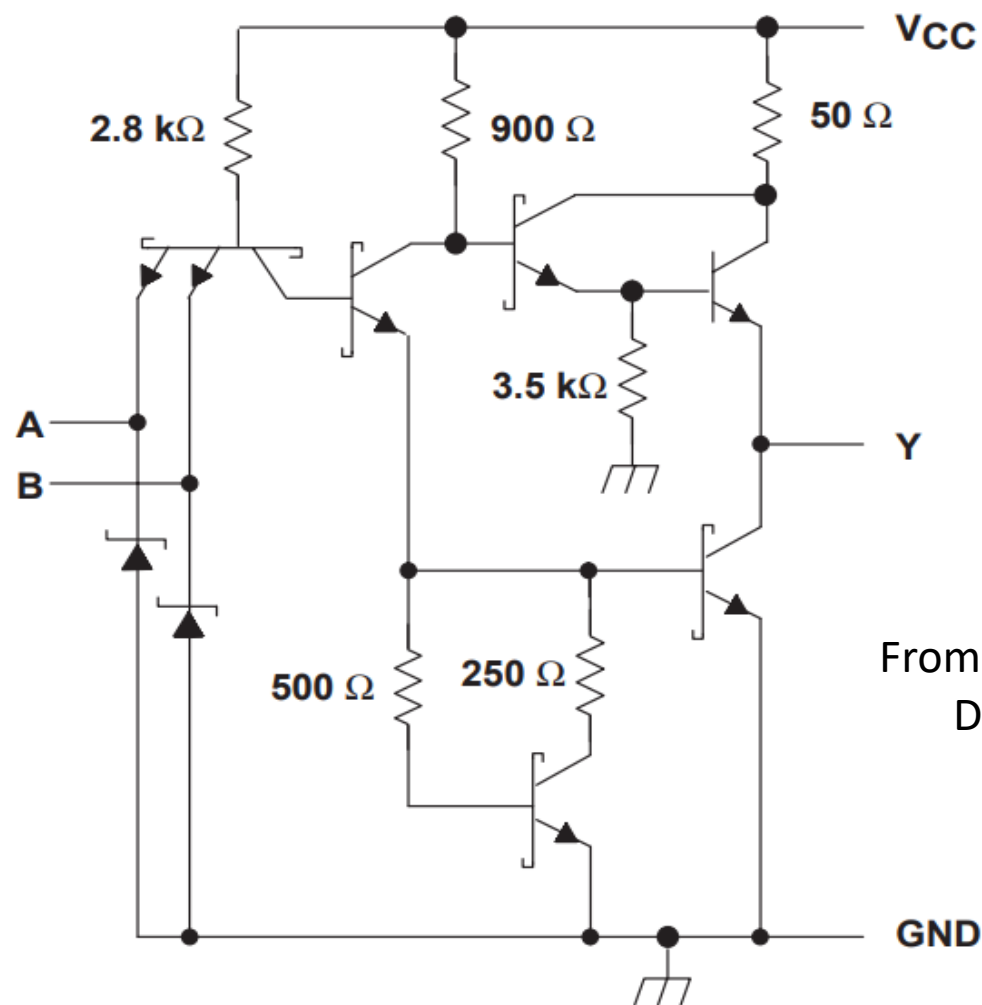
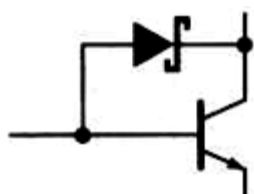


Input diodes
suppress ringing

Schottky TTL



Cut-in $\approx 0.35\text{V}$
(range 0.2-0.5V)



Qty.	Typ.	Max.	Unit
t_{PLH}	3	4.5	ns
t_{PHL}	3	5	ns

Under test condition
 $R_L=280\Omega$, $C_L=15\text{pF}$

From TI SN74S00
Datasheet

References:

- ❑ Herbert Taub, and Donald Schilling, Digital Integrated Electronics, McGraw Hill
- ❑ Grinich, V.H., and H.G. Jackson, Introduction to Integrated Circuits, McGraw-Hill
- ❑ Technical documents from <http://www.ti.com> accessed on Oct. 08, 2018